







SLOS377A - SEPTEMBER 2001- REVISED JULY 2003

FAMILY OF MICROPOWER RAIL-TO-RAIL INPUT AND OUTPUT OPERATIONAL AMPLIFIERS

FEATURES

- BiMOS Rail-to-Rail Input/Output
- Input Bias Current . . . 1 pA
- High Wide Bandwidth . . . 160 kHz
- High Slew Rate . . . 0.1 V/μs
- Supply Current . . . 7 μA (per channel)
- Input Noise Voltage . . . 90 nV/√Hz
- Supply Voltage Range . . . 2.7 V to 16 V
- Specified Temperature Range
 - -40°C to 125°C . . . Industrial Grade
- Ultra-Small Packaging
 - 5 Pin SOT-23 (TLV2381)

APPLICATIONS

- Portable Medical
- Power Monitoring
- Low Power Security Detection Systems
- Smoke Detectors

DESCRIPTION

The TLV238x single supply operational amplifiers provide rail-to-rail input and output capability. The TLV238x takes the minimum operating supply voltage down to 2.7 V over the extended industrial temperature range, while adding the rail-to-rail output swing feature. The TLV238x also provides 160-kHz bandwidth from only 7 μA . The maximum recommended supply voltage is 16 V, which allows the devices to be operated from (±8 V supplies down to ±1.35 V) two rechargeable cells.

The combination of rail-to-rail inputs and outputs make them good upgrades for the TLC27Lx family—offering more bandwidth at a lower quiescent current. The offset voltage is lower than the TLC27LxA variant.

To maintain cost effectiveness the TLV2381/2 are only available in the extended industrial temperature range. This means that one device can be used in a wide range of applications that include PDAs as well as automotive sensor interface.

All members are available in SOIC, with the singles in the small SOT-23 package, duals in the MSOP.

SELECTION GUIDE

DEVICE	V _S [V]	l <mark>Q/ch</mark> [μΑ]	VICR [V]	V _{IO} [mV]	I _{IB} [pA]	GBW [MHz]	SLEW RATE [V/µs]	V _n , 1 kHz [nV/√Hz]
TLV238x	2.7 to 16	10	-0.2 to $V_{S} + 0.2$	4.5	60	0.16	0.06	100
TLV27Lx	2.7 to 16	11	-0.2 to $V_{S} - 1.2$	5	60	0.16	0.06	100
TLC27Lx	4 to 16	17	-0.2 to V _S − 1.5	10/5/2	60	0.085	0.03	68
OPAx349	1.8 to 5.5	2	-0.2 to V _S + 0.2	10	10	0.070	0.02	300
OPAx347	2.3 to 5.5	34	-0.2 to V _S + 0.2	6	10	0.35	0.01	60
TLC225x	2.7 to 16	62.5	0 to V _S – 1.5	1.5/0.85	60	0.200	0.02	19

NOTE: All dc specs are maximums while ac specs are typicals.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



PACKAGE/ORDERING INFORMATION

PRODUCT	PACKAGE	PACKAGE CODE	SYMBOL	SPECIFIED TEMPERATURE RANGE	ORDER NUMBER	TRANSPORT MEDIA			
TLV2381ID	SOIC-8	D	23811		TLV2381ID	Tube			
TLVZ36TID	3010-6	D		20011	20011	20011	20011		TLV2381IDR
TLV2381IDBV	SOT-23	DBV	VBKI	–40°C to 125°C	TLV2381IDBVR	Tape and Reel			
TLVZ36TIDBV	301-23	DBV	VDNI	-40 C to 125 C	TLV2381IDBVT	Tape and Reel			
TLV2382ID	SOIC-8	D	23821		TLV2382ID	Tube			
1 LV 23021D	3010-0	D	23021		TLV2382IDR	Tape and Reel			

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V _S	16.5 V
Input voltage, V _I (see Notes 1 and 2)	
Output current, I _O	100 mA
Differential input voltage, V _{ID}	V _S
Continuous total power dissipation	See Dissipation Rating Table
Maximum junction temperature, T _J	150°C
Operating free-air temperature range, T _A : I suffix	–40°C to 125°C
Storage temperature range, T _{stq}	–65°C to 125°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	300°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Relative to GND pin.

2. Maximum is 16.5 V or V_S+0.2 V whichever is the lesser value.

DISSIPATION RATING TABLE

PACKAGE	(_o C/M) θ ¹ C	θJA (°C/W)	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	T _A = 85°C POWER RATING
D (8)	38.3	176	710 mW	370 mW
DBV (5)	55	324.1	385 mW	201 mW
DBV (6)	55	294.3	425 mW	221 mW



recommended operating conditions

		MIN	MAX	UNIT
Supply voltage (Va)	Dual supply	±1.35	±8	V
Supply voltage, (V _S)	Single supply	2.7	16	V
Input common-mode voltage range		-0.2	V _S +0.2	V
Operating free air temperature, TA	I-suffix	-40	125	°C

electrical characteristics at recommended operating conditions, V_S = 2.7 V, 5 V, and 15 V (unless otherwise noted)

dc performance

	PARAMETER	TEST CONDIT	IONS	T _A †	MIN	TYP	MAX	UNIT
\/10	Input offset voltage	V V (0 V) / /O	25°C		0.5	4.5	mV
VIO	input onset voltage	$V_{IC} = V_S/2,$ $V_O =$	= $VS/2$, $VO = VS/2$ = $100 \text{ k}\Omega$ $RS = 50 \Omega$	Full range			6.5	IIIV
ανιο	Offset voltage drift	1.5-		25°C		1.1		μV/°C
		$V_{IC} = 0 V \text{ to } V_S,$		25°C	54	69		
		$R_S = 50 \Omega$	V _S = 2.7 V	Full range	53			dB
		$V_{IC} = 0 \text{ V to V}_{S}-1.3 \text{ V},$	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	25°C	71	86		uВ
		$R_S = 50 \Omega$		Full range	70			
		$V_{IC} = 0 V \text{ to } V_{S},$	$R_S = 50 \Omega$ V _I C = 0 V to V _S -1.3 V,	25°C	58	74		dB
CMRR	Common-mode rejection ratio	$R_S = 50 \Omega$		Full range	57			
Civilata	Common-mode rejection ratio	$V_{IC} = 0 V \text{ to } V_{S}-1.3 V,$		25°C	72	88		
		$R_S = 50 \Omega$		Full range	70			
		$V_{IC} = 0 V \text{ to } V_S$		25°C	65	80		
		$R_S = 50 \Omega$		Full range	64			dB
		$V_{IC} = 0 \text{ V to V}_{S}-1.3 \text{ V},$	7 5 - 15 4	25°C	72	90		ub
		$R_S = 50 \Omega$		Full range	70			
			V _S = 2.7 V	25°C	80	100		
			VS = 2.7 V	Full range	77			dB
۸	Large-signal differential voltage	V _{O(PP)} =V _S /2,	V _S = 5 V	25°C	80	100		
AVD	amplification	RL = 100 kt2	vS = 3 v	Full range	77			
			V _S = 15 V	25°C	77	83		
			vS = 15 v	Full range	74			

[†] Full range is -40° C to 125° C.

input characteristics

	PARAMETER	TEST (CONDITIONS	TA	MIN	TYP	MAX	UNIT
				≤25°C		1	60	
lιO	Input offset current			≤70°C			100	pА
		$V_{IC} = V_S/2$,	$V_0 = V_S/2$,	≤125°C			1000	
		$R_L = 100 \text{ k}\Omega$,	$V_O = V_S/2$, $R_S = 50 \Omega$	≤25°C		1	60	
I _{IB}	Input bias current			≤70°C			200	pА
				≤125°C			1000	
r _{i(d)}	Differential input resistance		·	25°C		1000	, and the second	GΩ
CIC	Common-mode input capacitance	f = 1 kHz		25°C		8	·	рF



electrical characteristics at recommended operating conditions, V_S = 2.7 V, 5 V, and 15 V (unless otherwise noted) (continued)

power supply

	PARAMETER	TEST CONDITIONS	T _A †	MIN	TYP	MAX	UNIT
la a	Supply current (per channel)	Vo - Vo/2	25°C		7	10	
'DD	Зирріу сипені (рег спаннеі)	$V_O = V_S/2$	Full range			15	μΑ
PSRR	Power supply rejection ratio (AVe/AV/s)	V _S = 2.7 V to 16V, No load,	25°C	74	82		dB
FSKK	Power supply rejection ratio (ΔV _S /ΔV _{IO})	$V_{IC} = V_S/2 V$	Full range	70			uБ

[†] Full range is –40°C to 125°C for I suffix.

output characteristics

	PARAMETER	TEST CONDI	TIONS	T _A †	MIN	TYP	MAX	UNIT
			V _S = 2.7 V	25°C	200	160		
			VS = 2.7 V	Full range	220			
		$V_{IC} = V_S/2,$ $I_O = 100 \mu A$	V _S /2,	25°C	120	85		mV
		I _O = 100 μA	VS = 5 V	Full range	200			IIIV
\/ a	Output voltage swing from rail		Vs = 15 V	25°C	120	50		
۷o	Output voltage swing from fail		VS = 15 V	Full range	150			
			V _S = 5 V	25°C	800	420		
		$V_{IC} = V_{S}/2$	VS = 3 V	Full range	900			mV
		V _{IC} = V _S /2, I _O = 500 μA	Vs = 15 V	25°C	400	200		IIIV
			vS = 15 v	Full range	500			
IO	Output current	$V_O = 0.5 \text{ V from rail}$	V _S = 2.7 V	25°C		400		μΑ

[†] Full range is –40°C to 125°C for I suffix.

dynamic performance

)						
	PARAMETER	TEST CONDITIONS	TA	MIN TYP MAX	UNIT	
GBP	Gain bandwidth product	$R_L = 100 \text{ k}\Omega$, $C_L = 10 \text{ pF}$, $f = 1 \text{ kHz}$	25°C	160	kHz	
			25°C	0.06		
SR	SR Slew rate at unity gain	$V_{O(pp)} = 2 \text{ V}, R_L = 100 \text{ k}\Omega,$ $C_L = 10 \text{ pF}$	-40°C	0.05	V/μs	
		о_ = 10 рі	125°C	0.08	1	
φм	Phase margin	D. 400 kg C. 50 pF	25°C	62	0	
	Gain margin	$R_L = 100 \text{ k}Ω$, $C_L = 50 \text{ pF}$	25°C	6.7	dB	
	Sattling time (0.19/)	V(STEP)pp = 1 V, AV = -1, Rise	25°C	31	I	
t _S	Settling time (0.1%)	$V(STEP)pp = 1 V$, $AV = -1$, Rise $C_L = 10 pF$, $R_L = 100 k\Omega$ Fall	25 6	61	μs	

noise/distortion performance

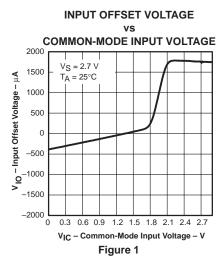
PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
V _n Equivalent input noise voltage	f = 1 kHz	25°C		90		nV/√ Hz

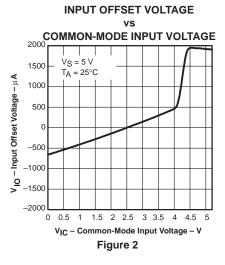


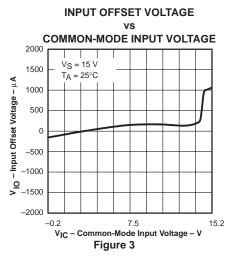
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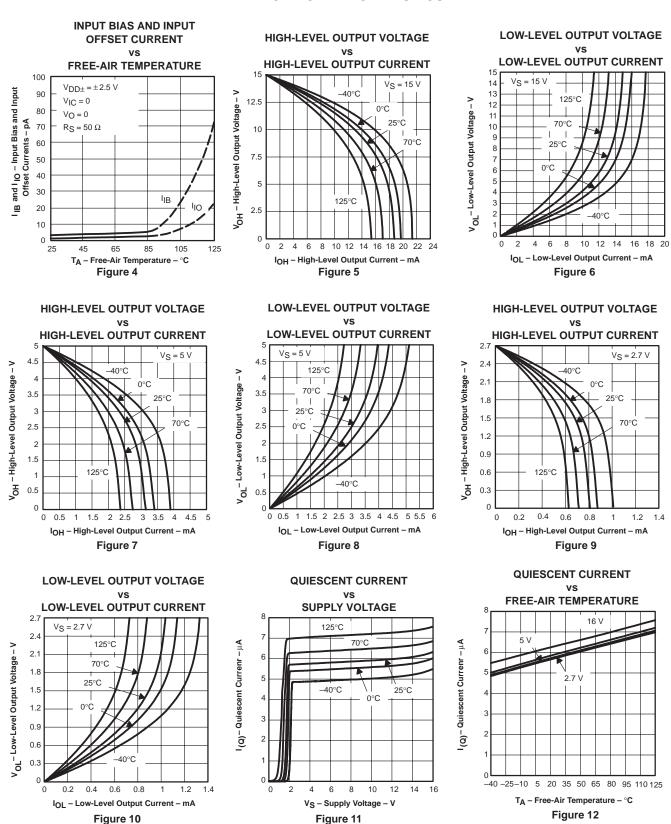
Table of Graphs

			FIGURE
VIO	Input offset voltage	vs Common-mode input voltage	1, 2, 3
I _{IB} /I _{IO}	Input bias and offset current	vs Free-air temperature	4
Vон	High-level output voltage	vs High-level output current	5, 7, 9
VOL	Low-level output voltage	vs Low-level output current	6, 8, 10
1-	Quiescent current	vs Supply voltage	11
IQ	Quiescent current	vs Free-air temperature	12
	Supply voltage and supply current ramp up		13
A _{VD}	Differential voltage gain and phase shift	vs Frequency	14
GBP	Gain-bandwidth product	vs Free-air temperature	15
φm	Phase margin	vs Load capacitance	16
CMRR	Common-mode rejection ratio	vs Frequency	17
PSRR	Power supply rejection ratio	vs Frequency	18
	Input referred noise voltage	vs Frequency	19
SR	Slew rate	vs Free-air temperature	20
VO(PP)	Peak-to-peak output voltage	vs Frequency	21
	Inverting small-signal response		22
	Inverting large-signal response		23
	Crosstalk	vs Frequency	24











SUPPLY VOLTAGE AND SUPPLY CURRENT RAMP UP 40 V_S - Supply Voltage - V/dc ٧s 10 ۷o $V_S = 0 \text{ to } 15 \text{ V},$ CC - Supply Current - µ A $R_L = 100 \Omega$, C_L = 10 pF, T_A = 25°C 15 5 t - Time - ms

Figure 13

DIFFERENTIAL VOLTAGE GAIN AND PHASE SHIFT

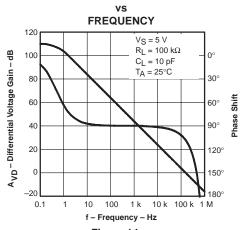
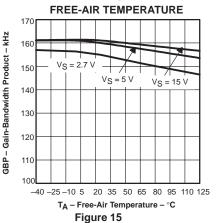
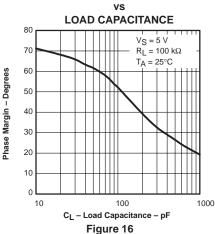


Figure 14

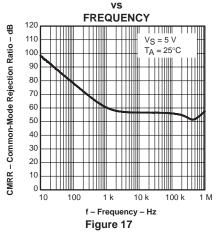
GAIN-BANDWIDTH PRODUCT FREE-AIR TEMPERATURE 170



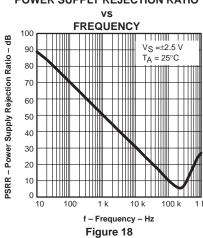
PHASE MARGIN



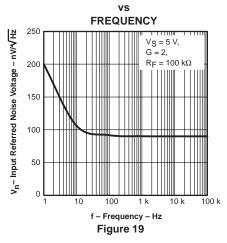
COMMON-MODE REJECTION RATIO



POWER SUPPLY REJECTION RATIO



INPUT REFERRED NOISE VOLTAGE



SLEW RATE

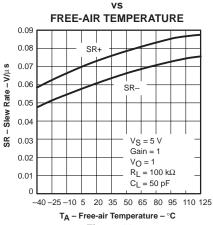
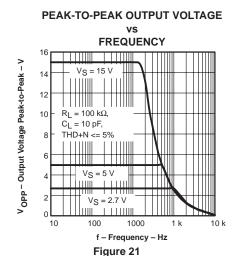
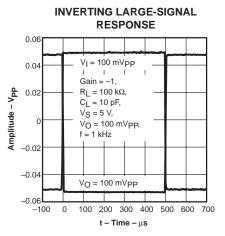


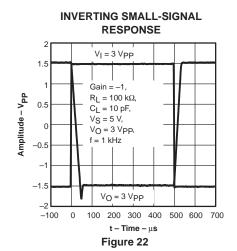
Figure 20











CROSSTALK vs **FREQUENCY** $V_S = 5 V$ $R_L = 2 k\Omega$ $C_L = 10 pF$ -20 $T_A = 25^{\circ}C$ -40 Channel 1 to 2 Crosstalk – dB -60 -80 -100 -120 -140 10 k 100 k 10 100 1 k f - Frequency - Hz

Figure 24



APPLICATION INFORMATION

offset voltage

The output offset voltage (V_{OO}) is the sum of the input offset voltage (V_{IO}) and both input bias currents (I_{IB}) times the corresponding gains. The following schematic and formula can be used to calculate the output offset voltage:

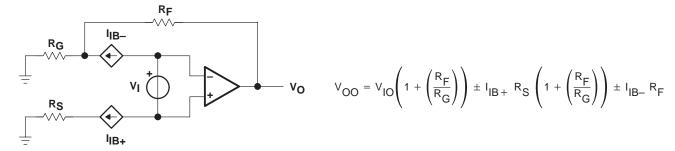


Figure 25. Output Offset Voltage Model

general configurations

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to accomplish this is to place an RC filter at the noninverting terminal of the amplifier (see Figure 26).

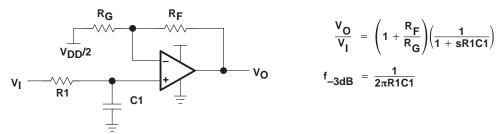


Figure 26. Single-Pole Low-Pass Filter

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter can be used for this task. For best results, the amplifier should have a bandwidth that is 8 to 10 times the filter frequency bandwidth. Failure to do this can result in phase shift of the amplifier.

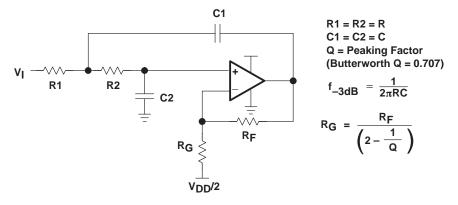


Figure 27. 2-Pole Low-Pass Sallen-Key Filter



APPLICATION INFORMATION

circuit layout considerations

To achieve the levels of high performance of the TLV238x, follow proper printed-circuit board design techniques. A general set of guidelines is given in the following.

- Ground planes—It is highly recommended that a ground plane be used on the board to provide all
 components with a low inductive ground connection. However, in the areas of the amplifier inputs and
 output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling—Use a 6.8-μF tantalum capacitor in parallel with a 0.1-μF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-μF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-μF capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets—Sockets can be used but are not recommended. The additional lead inductance in the socket pins
 will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board
 is the best implementation.
- Short trace runs/compact part placements—Optimum high performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible, thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.
- Surface-mount passive components—Using surface-mount passive components is recommended for high
 performance amplifier circuits for several reasons. First, because of the extremely low lead inductance of
 surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small
 size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray
 inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be
 kept as short as possible.



APPLICATION INFORMATION

general power dissipation considerations

For a given θ_{JA} , the maximum power dissipation is shown in Figure 28 and is calculated by the following formula:

$$P_{D} = \left(\frac{T_{MAX} - T_{A}}{\theta_{JA}}\right)$$

Where:

P_D = Maximum power dissipation of TLV238x IC (watts)

 T_{MAX} = Absolute maximum junction temperature (150°C)

 T_A = Free-ambient air temperature (°C)

 $\theta_{JA} = \theta_{JC} + \theta_{CA}$

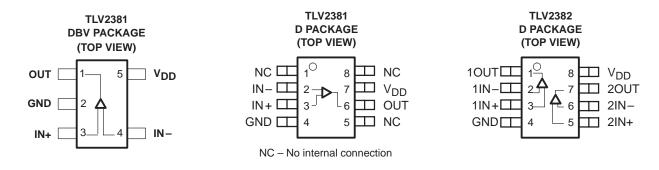
 θ_{JC} = Thermal coefficient from junction to case

 θ_{CA} = Thermal coefficient from case to ambient air (°C/W)

MAXIMUM POWER DISSIPATION FREE-AIR TEMPERATURE 2 Г」 = 150°C PDIP Package Low-K Test PCB 1.75 θ_{JA} = 104°C/W Maximum Power Dissipation - W 1.5 MSOP Package Low-K Test PCB **SOIC Package** θ_{JA} = 260°C/W 1.25 Low-K Test PCB = 176°C/W 0.75 0.5 0.25 SOT-23 Package Low-K Test PCB $\theta_{JA} = 324^{\circ}\text{C/W}$ -55-40-25-10 5 20 35 50 65 80 95 110 125 T_A - Free-Air Temperature - °C

NOTE A: Results are with no air flow and using JEDEC Standard Low-K test PCB.

Figure 28. Maximum Power Dissipation vs Free-Air Temperature





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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	,	
	(-)	(=/			(5)	(4)	(5)		(6)
TLV2381ID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23811
TLV2381ID.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23811
TLV2381IDBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VBKI
TLV2381IDBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	VBKI
TLV2381IDBVT	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	VBKI
TLV2381IDBVT.A	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	VBKI
TLV2381IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23811
TLV2381IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23811
TLV2382ID	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821
TLV2382ID.A	Active	Production	SOIC (D) 8	75 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821
TLV2382IDG4	Active	Production	SOIC (D) 8	75 TUBE	-	Call TI	Call TI	-40 to 125	
TLV2382IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821
TLV2382IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821
TLV2382IDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821
TLV2382IDRG4.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	23821

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	-
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2381IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV2381IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TLV2381IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2382IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2382IDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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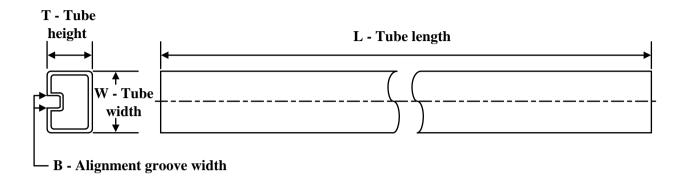
*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2381IDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TLV2381IDBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
TLV2381IDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV2382IDR	SOIC	D	8	2500	353.0	353.0	32.0
TLV2382IDRG4	SOIC	D	8	2500	353.0	353.0	32.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TLV2381ID	D	SOIC	8	75	507	8	3940	4.32
TLV2381ID.A	D	SOIC	8	75	507	8	3940	4.32
TLV2382ID	D	SOIC	8	75	507	8	3940	4.32
TLV2382ID.A	D	SOIC	8	75	507	8	3940	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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